Abstracts

A High Gain Silicon AGC Amplifier with a 3 dB Bandwidth of 4 GHz

L.C.N. de Vreede, A.C. Dambrine, J.L. Tauritz and R.G.F. Baets. "A High Gain Silicon AGC Amplifier with a 3 dB Bandwidth of 4 GHz." 1994 Transactions on Microwave Theory and Techniques 42.4 (Apr. 1994, Part I [T-MTT]): 546-552.

In this paper, the design and realization of an integrated high frequency AGC amplifier in BiCMOS technology are discussed. The amplifier has 36 dB voltage gain, 4 GHz bandwidth, dynamic range exceeding 50 dB, low spectral distortion and low power consumption. The amplifier is suitable for application in wide-band optical telecommunication systems.

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